

GlobalFoundries Product/Patent Marking Document

GF Product	Patents	Title	Issue Date
14LPP / 12LP	US6664604	Metal gate stack with etch stop layer	12-16-2003
	US7750418	Introduction of metal impurity to change workfunction of conductive electrodes	7-6-2010
	US8912603	Semiconductor device with stressed fin sections	12-16-2014
	US9105643	Bit cell with double patterned metal layer structures	8-11-2015